

CSE-411

Name: AYON ROY

ID : 201714018

Sec: B

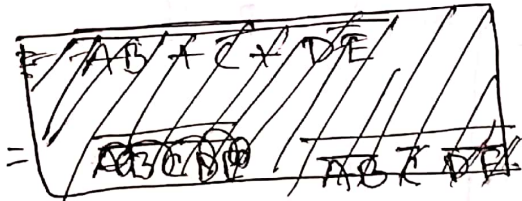
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Ans. to the ques. no. - 01

$$Y = AB + C + DE \text{ So,}$$



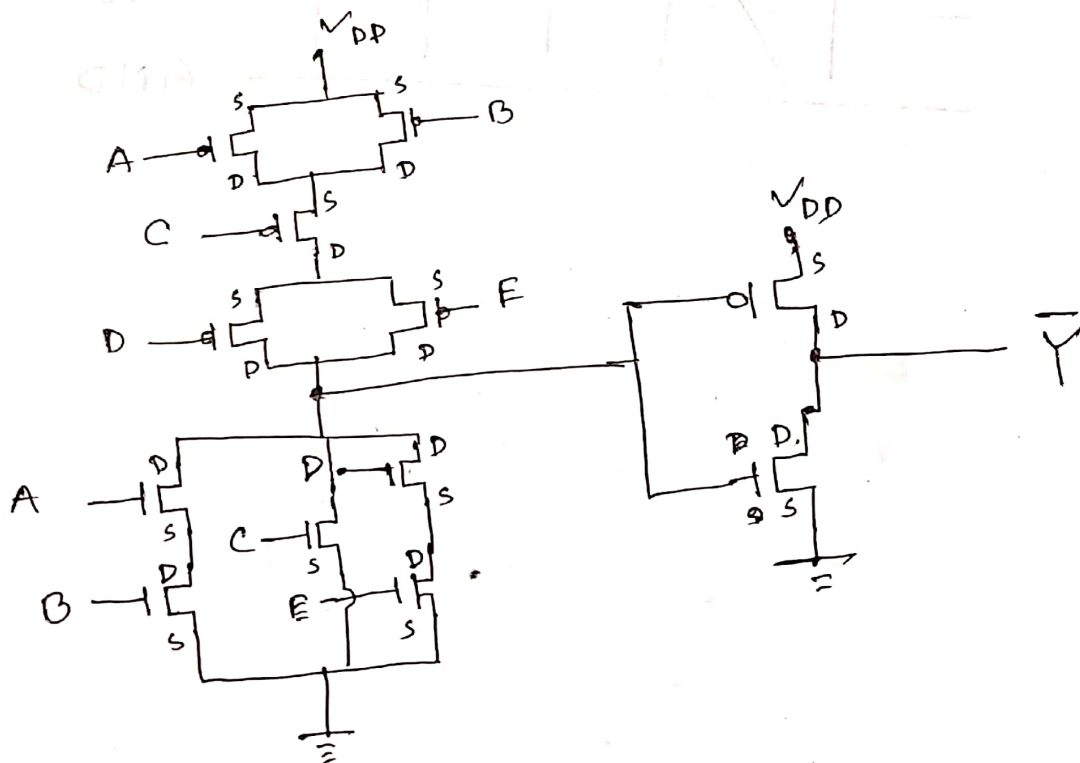
$$\overline{A+B}$$

$$\overline{AB}$$

$$A+B = \overline{\overline{A+B}}$$

$$\overline{Y} = \overline{AB + C + DE} \quad (\text{since we need complementary})$$

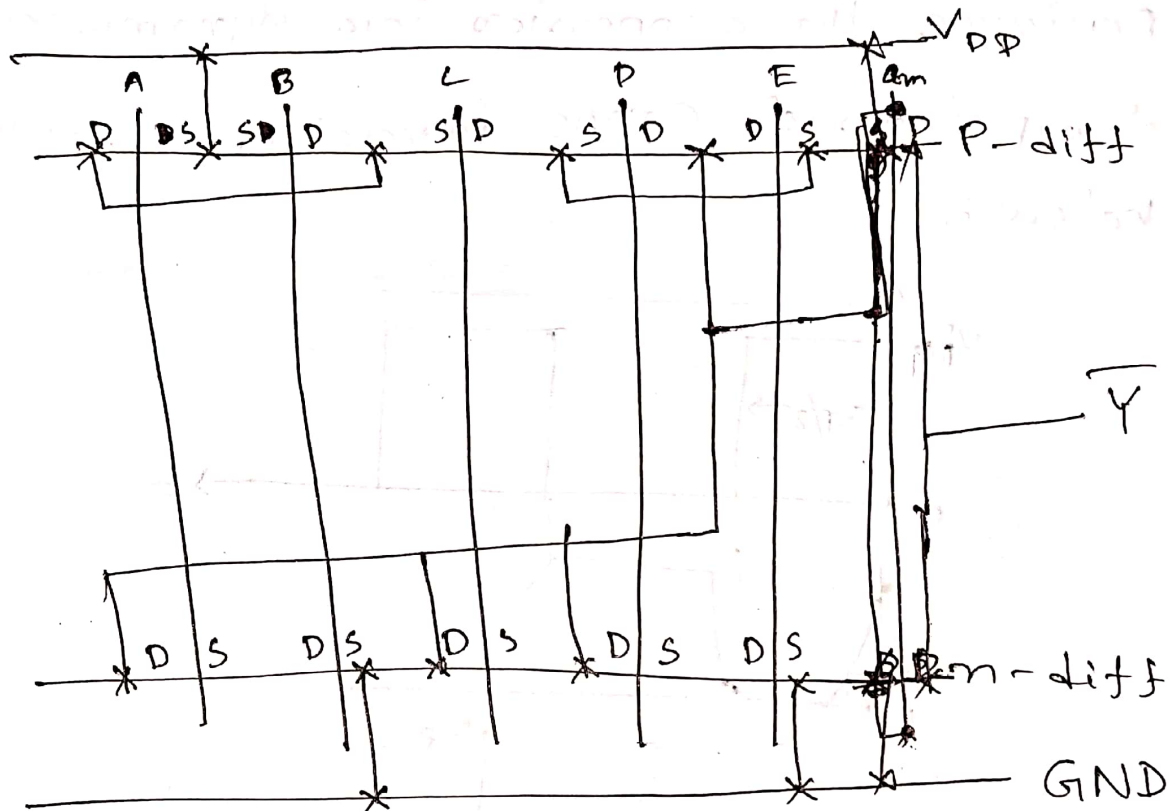
So, CMOS circuit diagram:



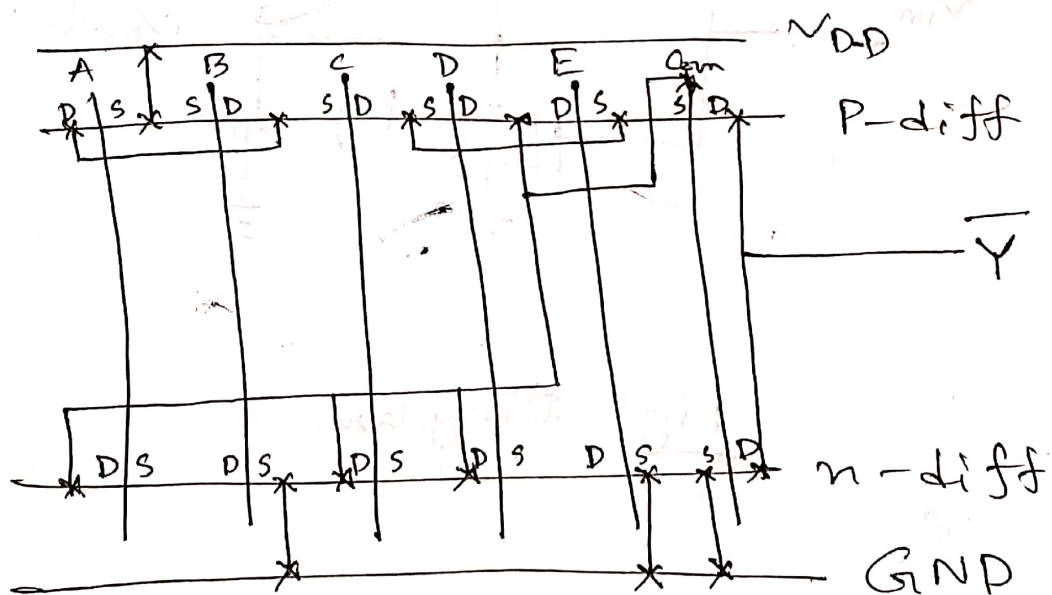
Circuit Diagram

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Ayan Roy
201714018

Stick diagram is drawn below :



with cleaning



Stick Diagram final

Ans. to the ques. no. - 02

Deriving the expression for dynamic power dissipation of CMOS inverter is given below:

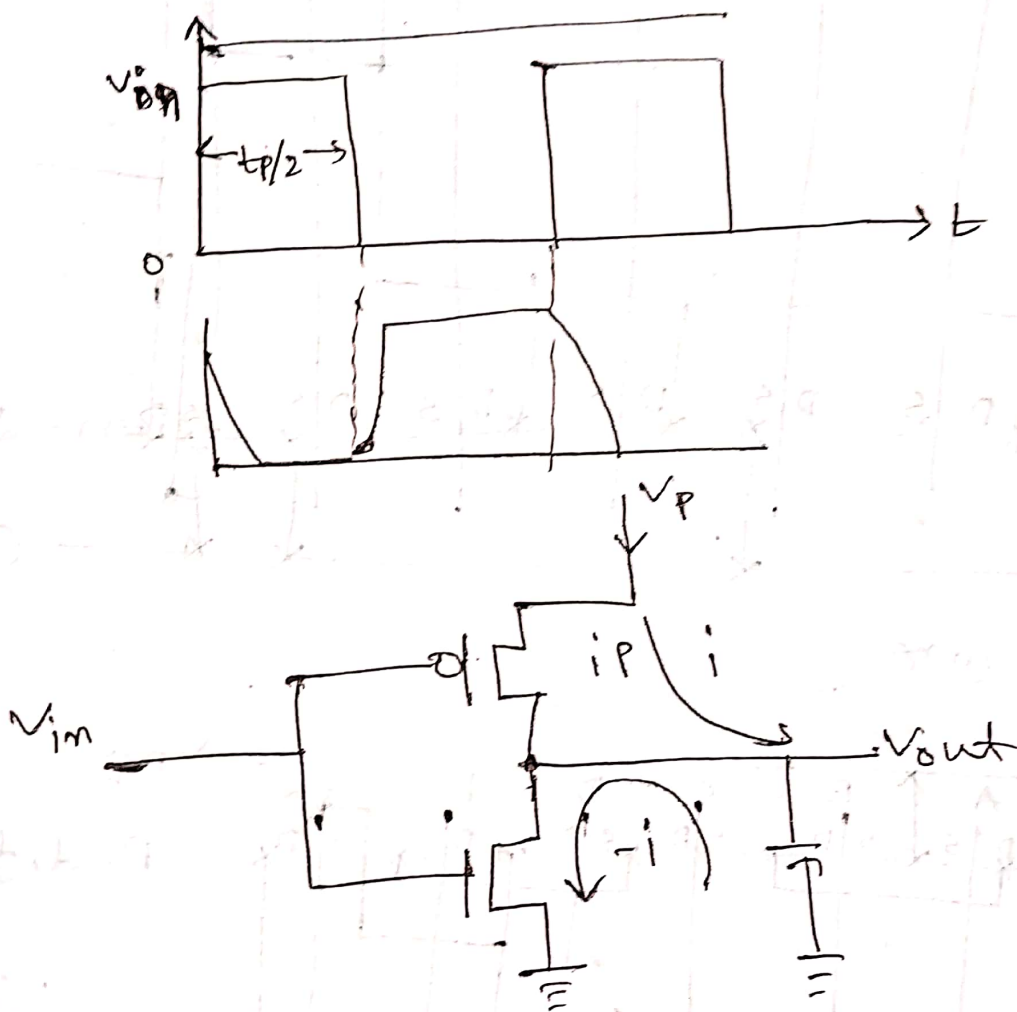


Fig: Diagram.

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dynamic Power dissipation, P_d

$$\begin{aligned}
 P_d &= \frac{1}{t_P} \int_0^{t_P/2} i_n(t) V_0 dt + \frac{1}{t_P} \int_{t_P/2}^{t_P} i_P(t) (V_P - V_0) dt \\
 &= \frac{C_L}{t_P} \left[\int_{V_P}^0 -V_0 dV_0 + \int_0^{V_P} (V_P - V_0) dV_0 \right] \left[\because i_n(t) = C_L \frac{dV_0}{dt} \right] \\
 &= \frac{C_L}{t_P} \int_0^{V_P} (V_0 + V_P - V_0) dV_0 \\
 &= \frac{V_P C_L}{t_P} \int_0^{V_P} 1 \cdot dV_0 \\
 &= \frac{V_P^2 C_L}{t_P}
 \end{aligned}$$

$\therefore P_d = \frac{C_L V_P^2}{t_P}$ and we know, $f_P = \frac{1}{t_P}$ So,

$$P_d = f_P C_L V_P^2$$

So, $P_d \propto f_P, C_L$

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Ayon Roy
20/12/14018

So, P_d is proportional to both frequency and load capacitance.

So, if both load ~~balance~~ capacitance and frequency are doubled then dynamic power dissipation will be 4x.

$$\begin{aligned}\text{So, } P'_d &= 4 \times 5\text{mW} \\ &= 20\text{mW}\end{aligned}$$

Ans

Ans. to the ques. no. - 03

Drawing the cross section of a CMOS inverter:

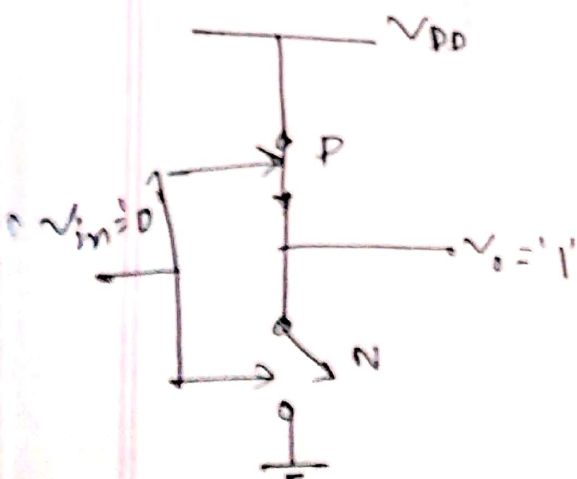
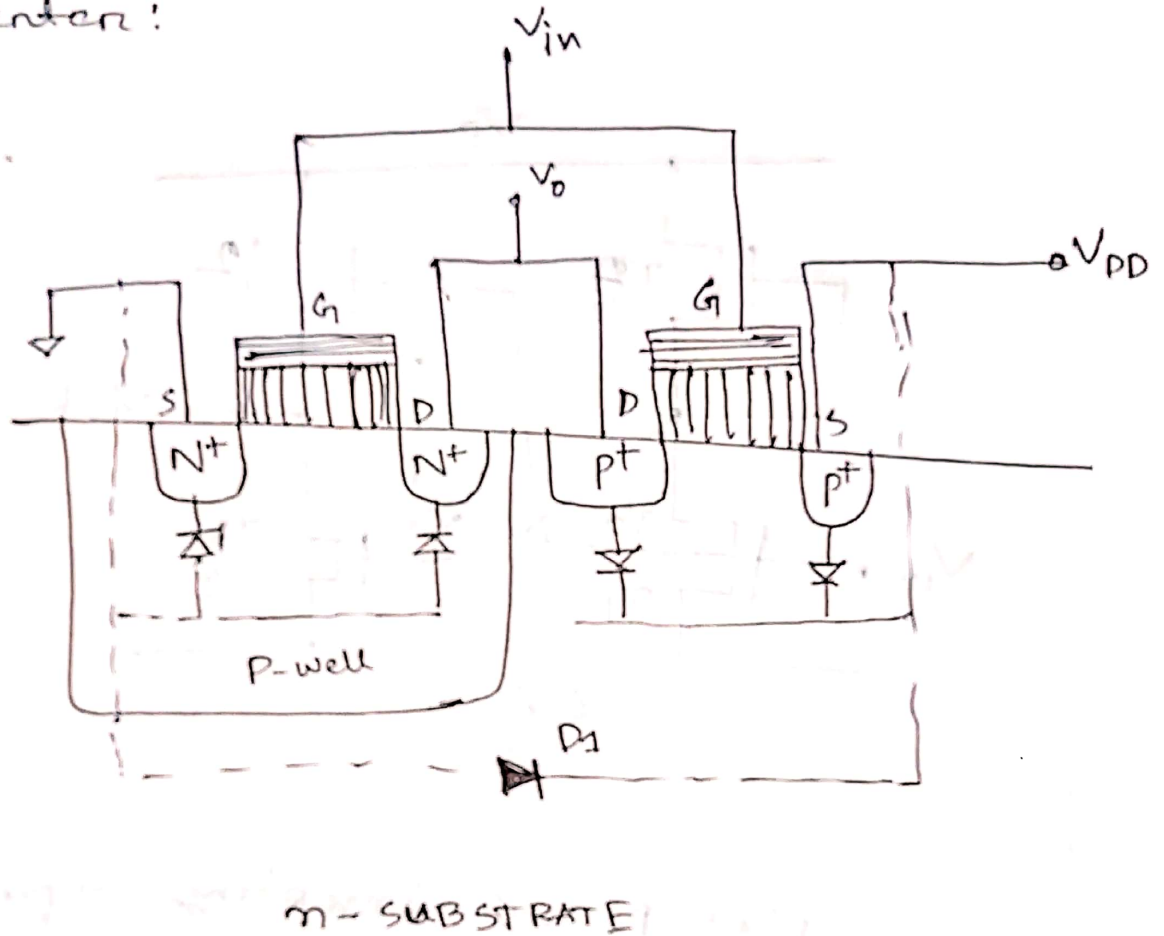


fig: cross section of CMOS inverter.

Ans. to the ques. no. - 04

Drawing the NMOS inventing super-buffer circuit below:

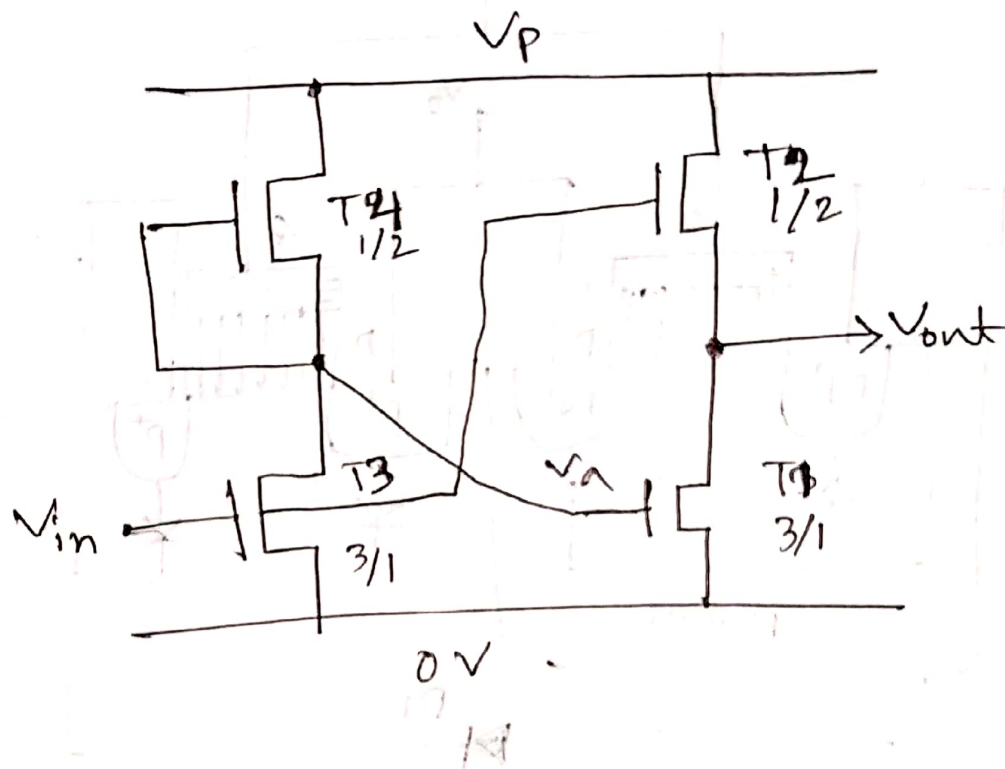


Fig: NMOS inventing superbuffer